



(51) International Patent Classification:

G01T 1/24 (2006.01) G21K 1/10 (2006.01)
G01T 1/29 (2006.01) G21K 1/02 (2006.01)

(21) International Application Number:

PCT/SE2016/050829

(22) International Filing Date:

5 September 2016 (05.09.2016)

(25) Filing Language:

English

(26) Publication Language:

English

(30) Priority Data:

62/232,030 24 September 2015 (24.09.2015) US

(71) Applicant: **PRISMATIC SENSORS AB** [SE/SE];
Roslagstullsbacken 21, SE-106 91 Stockholm (SE).

(72) Inventors: **DANIELSSON, Mats**; Guldgränd 5, 187 44
Täby (SE). **KARLSSON, Staffan**; Ståltrådsvägen 34, 168
68 Bromma (SE).

(74) Agent: **AROS PATENT AB**; Box 1544, SE-751 45
Uppsala (SE).

(81) Designated States (unless otherwise indicated, for every

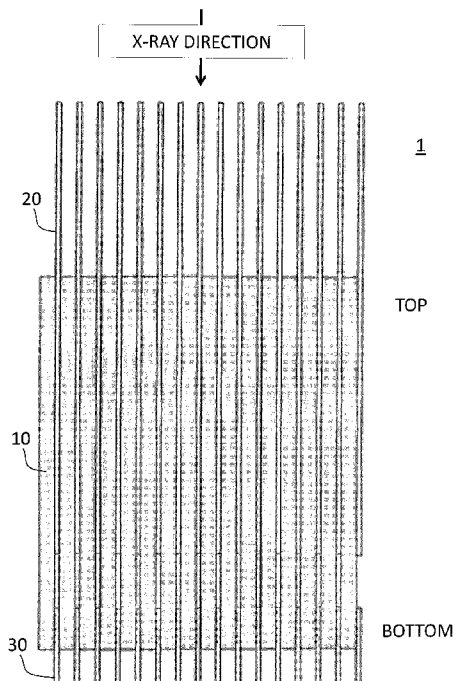
kind of national protection available): AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BN, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IR, IS, JP, KE, KG, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PA, PE, PG, PH, PL, PT, QA, RO, RS, RU, RW, SA, SC, SD, SE, SG, SK, SL, SM, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States (unless otherwise indicated, for every

kind of regional protection available): ARIPO (BW, GH, GM, KE, LR, LS, MW, MZ, NA, RW, SD, SL, ST, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, KM, ML, MR, NE, SN, TD, TG).

[Continued on next page]

(54) Title: MODULAR X-RAY DETECTOR



(57) Abstract: There is provided a detector module (1) for a modular x-ray detector, wherein the detector module (1) comprises multiple x-ray detector substrates (10) and associated anti-scatter collimators (20). Each x-ray detector substrate (10) has a number of detector diodes, and each x-ray detector substrate (10) has an associated anti-scatter collimator (20). Each x-ray detector substrate (10) has an integrated circuit (30) for collecting x-ray signals from the diodes attached to the x-ray detector substrate at the bottom of the x-ray detector substrate assuming the top is where the x-rays enter, and the associated anti-scatter collimator (20) is placed above the integrated circuit (30).

Fig 2

WO 2017/052443 A1

Published:

— *with international search report (Art. 21(3))*

Modular x-ray detector

TECHNICAL FIELD

The proposed technology generally relates to x-ray detectors and more specifically to a modular x-ray detector and a detector module for such a modular x-ray detector.

BACKGROUND

When constructing x-ray detectors, the main challenges are to achieve high detection efficiency, enable a modular arrangement of detectors and/or make sure packaging and wiring is possible so that the detector can be efficiently produced. It is furthermore beneficial if all requirements can be met at the same time, which is a challenge since in part the requirements contradict each other. For example the wiring and packaging required for a modular arrangement often means you have to sacrifice active detector area such that the geometrical efficiency is reduced.

Furthermore the x-ray detector in most cases has to be integrated with an anti-scatter collimator or grid to eliminate scatter from the object and/or between detector modules. It is also desirable that sensitive integrated circuits are protected from direct radiation since a high accumulated dose could negatively impair the functioning of the circuits.

At the same time each detector module and anti-scatter grid should preferably be accurately aligned to the incident x-rays from the source.

State-of-the art detectors in for example Computed Tomography are based on a scintillator converting the x-rays to visible light that is detected by a dedicated photo diode that integrate the signal for many x-rays. The photo diode is connected to integrated circuits that digitize the produced current and this value

is used to calculate grey scale values displayed in the x-ray image. A one-dimensional or two dimensional anti scatter grid is placed on top of the scintillators and diodes. To avoid cross talk a trench separates each scintillator-diode assembly. The anti-scatter collimator is positioned to match the trenches in order to minimize any dead area. There are several ways to solve the packaging and wiring challenges: to connect the diode to the integrated circuit, to provide power and data transmission. There are good examples how these challenges can be addressed. One example is disclosed in reference [1] where a fully modular arrangement is presented that can be tiled in two dimensions. Another example for an interconnect and packaging method is presented in reference [2] where an elastomer conducting contact is configured to provide a high-voltage anode signal.

The last years a lot of research focus both in academia and in industry has been focused on how to provide x-ray detectors with higher spatial and contrast resolution. One of the most promising ways to achieve this is through photon counting spectral detectors. So far these imaging detectors are only available for mammography in early breast cancer detection, see reference [3], but the next use may be in Computed Tomography. Two different solutions have emerged, one based on heavy detector elements such as CdTe or CdZnTe presented for example in reference [4] and another based on Silicon as detector material as outlined in reference [5].

In a Silicon detector assembly such as outlined in reference [5] the challenges in detection efficiency and modularity are very different compared to assemblies with heavy elements as detector material since the Silicon detectors need to be much longer (around 30-40 times) in the direction of the incoming x-rays in order to absorb a major fraction of the x-rays. This means the geometry and mechanical constraints are very different.

SUMMARY

It is an object to provide an improved detector module for a modular x-ray detector.

It is also an object to provide an improved modular x-ray detector based on such detector modules.

These and other objects are met by embodiments of the proposed technology.

In a first aspect of the proposed technology, there is provided a detector module for a modular x-ray detector, wherein the detector module comprises multiple x-ray detector substrates and associated anti-scatter collimators. Each x-ray detector substrate has a number of detector diodes, and each x-ray detector substrate has an associated anti-scatter collimator. Further, each x-ray detector substrate has an integrated circuit for collecting x-ray signals from the diodes attached to the x-ray detector substrate at the bottom of the x-ray detector substrate assuming the top is where the x-rays enter, and the associated anti-scatter collimator is placed above the integrated circuit.

This type of detector module enables an efficient way of building a modular x-ray detector.

In a second aspect of the proposed technology, there is thus provided a modular x-ray detector comprising a number of detector modules of the first aspect.

Other advantages will be appreciated when reading the detailed description.

BRIEF DESCRIPTION OF DRAWINGS

FIG. 1 is a schematic diagram illustrating an example of an x-ray detector module and a corresponding modular detector assembly.

FIG. 2 is a schematic diagram illustrating an example of a detector module for a modular x-ray detector.

Fig 3 is a schematic diagram illustrating a close-up of the example module shown in Fig 2.

Fig 4 is a schematic diagram illustrating an example of how to get a tapered geometry where anti-scatter collimators and detector substrate are pointing back to the source to provide an overall curved detector geometry.

Fig 5 is a schematic diagram illustrating an example of how the ASIC can be flip chipped to the silicon detector substrate where input signals are routed from the individual diodes to the ASIC inputs.

Fig 6 is a schematic diagram illustrating an example of a view from the side showing that there is space for wire-bonds, passive components and cabling below the detector substrate.

Fig 7 is a schematic diagram illustrating an example of an architecture for electronic readout of data and for distributing control commands to detector modules.

DETAILED DESCRIPTION

An illustrative, non-limiting example of the present invention is illustrated in Fig. 1 where an x-ray detector module and a corresponding modular detector assembly 100 is displayed where modules can be tiled to achieve any area of the full detector assembly as long as boundary conditions of maximum power and data transfer rates can be handled.

FIG. 2 is a schematic diagram illustrating an example of a detector module for a modular x-ray detector. In this example, the detector module 1 comprises multiple x-ray detector substrates 10 and associated anti-scatter collimators 20.

Each x-ray detector substrate 10 has a number of detector diodes, and each x-ray detector substrate 10 has an associated anti-scatter collimator 20. Further, each x-ray detector substrate 10 has an integrated circuit 30 for collecting x-ray signals from the diodes attached to the x-ray detector substrate at the bottom of the x-ray detector substrate 10 assuming the top is where the x-rays enter, and the associated anti-scatter collimator 20 is placed above the integrated circuit 30.

This type of detector module enables an efficient way of building a modular x-ray detector. Embodiments of the modular x-ray detector have several structural advantages, as will be appreciated from the examples described herein.

In a second aspect of the proposed technology, there is thus provided a modular x-ray detector 100 comprising a number of detector modules 1 of the first aspect.

The detector module may be embodied in many different variations.

By way of example, the integrated circuits may be Application Specific Integrated Circuits, ASICs.

For example, the ASIC may be extending over the edge of the x-ray detector substrate so that part of the ASIC is outside of the silicon detector substrate to enable connection of power and data transfer to the ASIC without having to route this on the silicon detector substrate.

The signals may for example be routed from the individual diodes to inputs of the ASIC.

Optionally, power lines and data transfer lines are wire-bonded to power and data transfer pads at the ASIC outside the substrate, or a redistribution layer on the substrate is used to connect to power, data transfer pads and to input signal

pads and redistribute the input signals from the x-ray detector substrate to the ASIC.

As a complement, a heat conductor may be attached to the ASIC as a means for cooling.

By way of example, the anti-scatter collimators may be anti-scatter foils or plates.

For example, anti-scatter foils may be positioned between the x-ray detector substrates.

The anti-scatter foils may be made of a heavy material such as Tungsten.

In a particular example, the integrated circuits are Application Specific Integrated Circuits, ASICs, and the anti-scatter collimators are Tungsten foils and the ASICs are placed on the x-ray detector substrate under the Tungsten foils to minimize so-called dead area in the detector and the ASICs will be protected from direct radiation.

Preferably, a tapered geometry in which, for each x-ray detector substrate, the x-ray detector substrate and the associated anti-scatter collimator are pointing back to the source may be provided for by means of a spacer placed at the silicon detector substrate or at the anti-scatter collimator.

Normally, a number of x-ray detector substrates are tiled with respect to each other to form a detector module.

As an example, each x-ray detector substrate and corresponding integrated circuit may be formed as a sensor multi-chip module, MCM, assembly, and a multitude of sensor MCM assemblies may then be connected into the detector module.

For example, the detector module may be sub-divided into a number of detector tiles, where each detector tile includes a number of sensor MCM assemblies, for example as illustrated in Fig. 7.

In a particular example, each detector tile includes a circuit for demultiplexing commands from the corresponding detector module to the detector tile to reduce the number of connections between the detector tile and the detector module, for example as illustrated in Fig. 7.

Typically, the commands are control commands directed to the sensor MCM assemblies.

The detector module may comprise a number of data storage circuits and data processing circuits, wherein each detector tile is managed by a data processing circuit.

For example, the detector module may include a control and communication circuit for distributing control commands for the sensor MCM assemblies and controlling the readout of stored scanning data from the data storage circuits.

In a particular example, the x-ray detector substrates are Silicon detector substrates.

For a better understanding, the proposed technology will now be described with reference to non-limiting illustrative examples.

In order to avoid any dead area the integrated circuit (ASICs) collecting the x-ray signals from the diodes has been attached to the x-ray detector diode substrate at the bottom side assuming top side is where the x-rays enter. The anti-scatter collimator is e.g. made up of Tungsten foils in between each Silicon detector substrate. In order to minimize so called dead area in the detector (area which is not functioning as a detector such is the mechanical support, the Tungsten foils, air gaps etc.) the ASICs for collecting the x-ray signals from the diodes are placed under the Tungsten foils. This also means the ASICs will be protected from direct radiation. In order not to be significantly thicker than the Tungsten foils the ASICs are thinned down to 50- 100 um.

In a particular example, the ASIC is flip chipped to the Silicon detector substrate and each diode is connected through a trace to a dedicated ASIC input. Moreover the ASIC is sticking out over the edge of the silicon detector substrate. This gives space for larger components like capacitors that has to be situated close to the ASIC to optimize reliability and noise performance.

This means that thick traces for power, which would make the silicon substrate more expensive to produce, is not required. The power connections can be provided for by other means to the ASIC. For example power lines could be wire-bonded to supply pads at the ASIC.

Another solution would be to use a redistribution layer that would connect to power, data transfer pads and to input signal pads and redistribute the signals from the ASIC to the Silicon detector substrate.

Behind the Silicon detector substrate there will be space for electronic components such as capacitances that should be positioned close to the electronic. It is also possible to put an x-ray absorber in a heavy material such as Tungsten or Molybdenum after the Silicon to avoid that any x-rays transmitted through the silicon is penetrating further into the assembly. It is also possible to put radiation-protected material around the integrated circuit to minimize any radiation damage.

As a means for cooling a heat conductor, preferably with matching heat expansion co-efficient to Silicon, can be attached to the ASIC and the heat produced by the ASIC power can be transferred to a place where it can easily be taken care of by standard air or liquid cooling means.

FIG. 1 is a schematic diagram illustrating an example of an x-ray detector module and a corresponding modular detector assembly. Fig 1 shows an example of a module and how such modules could build up a corresponding modular detector assembly having a full detector area of desired size. Note that the modules are pointing back to the x-ray source.

FIG. 2 is a schematic diagram illustrating an example of a detector module for a modular x-ray detector. Fig 2 thus displays an example of a module design. Starting from the top, the anti-scatter foils made of a heavy material like W is displayed, the foils are typically significantly thinner than the silicon detector substrate which is the active detector volume consisting of diodes. The x-ray detector substrate is positioned in-between the foils. The x-ray detector substrate may for example be in the order of 0.5 mm thick. Both foils and x-ray detector substrate is pointing back to the x-ray source to avoid parallax errors and shadowing from the anti-scatter foils. At the bottom the ASICs are indicated, they are typically as thin as the W foils and positioned behind those foils (looking from above)

Fig 3 is a close-up of Fig 2 showing the anti-scatter foils, the silicon detector substrate and the ASICs.

Fig 4 shows an example of how to get a tapered geometry when Tungsten and Silicon detector substrate are pointing back to the source by placing a spacer as for example a stud bond at the silicon detector substrate or at the anti-scatter grid.

In order for all Tungsten foils and Silicon detectors to precisely point back to the source a spacer between each element may be used. Due to this spacer the whole detector will be curved. Fig. 4 shows an example of how to achieve a tapered geometry by placing a spacer of for example a stud bump at the silicon detector substrate or at the Tungsten foil

Fig 5 displays an example of how the ASIC can be flip chipped to the silicon detector substrate where input signals are routed from the individual diodes to the ASIC inputs. Part of the ASIC is outside of the silicon detector substrate to enable connection of power and data transfer to the ASIC without having to route this on the silicon detector substrate.

Fig 6 is a view from the side showing that there is space for wire-bonds, passive components and cabling behind the silicon detector substrate. Heat conductor is not indicated in the image but can be attached to ASIC.

Fig 7 is a schematic diagram illustrating an example of the architecture for electronic readout of data.

A significant challenge is to read out the data for a multitude of x-ray detector modules.

An example of a possible architecture solution is shown in Fig 7. In this example a multitude of sensor MCM (Multi-Chip Module) assemblies are connected into one detector module. In this context, a sensor MCM assembly means silicon substrate detector and ASIC assembly.

For example, each detector module may be managed by a small FPGA (Field Programmable Gate Array) or similar circuit that handles clock distribution, loading of configuration data and distribution of commands to the sensor MCMs.

By way of example, a full detector can contain several 10:th of thousands ASICs thus connecting and setting up / programming all ASICs in a detector is a particular challenge.

Each detector module may be based on the sensor MCMs in steps, for example by arranging sensor MCMs on detector tiles and then building a detector module based on a number of detector tiles. In other words, each detector module may include a number of detector tiles, where each detector tile includes a number of sensor MCM assemblies.

In order to physically fit all connections and meet bandwidth demands a scheme illustrated in figure 7 can be used.

Each tile includes a small FPGA for demultiplexing of low information content signals such as clock and/or commands from the module to the tile. As indicated in figure 7 this can for example reduce the number of connections between tile and module from $42+21$ to $3+21$.

Local memories (3*DDR in fig 7) distributed in the modules stores/buffers data to relax bandwidth demands on downstream connections. All these memories are read out at a lower rate when acquisition is finished. This arrangement can reduce the number of connections from the module to the motherboard, in the example in figure 7 the reduction is from 72 ($3*24$) to 8 connections.

Local memories and processors/FPGAs are preferably used to handle setup of the circuits, in order to parallelize the task. A single source configuring 10:ths of thousands of ASICs is too slow. A preferred way might be to broadcast common information parts and send specific information separately. Calibration may be handled locally on the module level, including calculation, storage, loading and so forth.

By way of example, the detector mother board has the control of the complete system, and can be regarded as an overall control system and link to external systems.

In a particular example, three detector tiles are put together into a detector module. Each detector tile is managed by a processing circuit with associated memory/data storage, e.g. a data storage FPGA or similar circuit. This FPGA/circuit stores all scanning data from one sensor MCM assembly locally and sends control commands intended for the sensor MCM assembly. A control and communication FPGA or similar circuit may also be placed in the detector module. At power up, this unit manages configuration of other FPGAs/circuits in the detector module, using configuration data stored in a local FLASH. When the system is up and running, it distributes the control commands for the sensor MCM assemblies and controls the readout of stored scanning data from the three

processing circuits with associated memory/data storage, e.g. data storage FPGAs. The data is sent to the detector mother board.

By way of example, commands may be broadcast to all detector modules for synchronous execution, or individually addressed for other tasks. It controls the readout of the scanning data from the detector modules, downloading of calibration data to the sensor MCM, etc.

From the detector mother board the data can be further transmitted to one or more external computers for post-processing and/or image reconstruction.

The embodiments described above are merely given as examples, and it should be understood that the proposed technology is not limited thereto. It will be understood by those skilled in the art that various modifications, combinations and changes may be made to the embodiments without departing from the present scope as defined by the appended claims. By way of example, it will be appreciated that the arrangements described herein can be implemented, combined and re-arranged in a variety of ways. In particular, different part solutions in the different embodiments can be combined in other configurations, where technically possible.

References

- [1] US Patent 7,582,879
- [2] US Patent 7,560,702
- [3] M. Danielsson, H. Bornefalk, B. Cederström, V. Chmill, B. Hasegawa, M. Lundqvist, D. Nygren and T. Tabár, "Dose-efficient system for digital mammography", *Proc. SPIE, Physics of Medical Imaging*, vol. 3977, pp. 239-249 San Diego, 2000
- [4] C. Xu, M. Danielsson and H. Bornefalk, "Evaluation of Energy Loss and Charge Sharing in Cadmium Telluride Detectors for Photon-Counting Computed Tomography", *IEEE Transactions on Nuclear Science*, vol. 58, no. 3, pp. 614 – 625, June 2011
- [5] US Patent 8,183,535

CLAIMS

1. A detector module (1) for a modular x-ray detector, wherein the detector module (1) comprises multiple x-ray detector substrates (10) and associated anti-scatter collimators (20),
wherein each x-ray detector substrate (10) has a number of detector diodes, and each x-ray detector substrate has an associated anti-scatter collimator (20),
wherein each x-ray detector substrate (10) has an integrated circuit (30) for collecting x-ray signals from the diodes attached to the x-ray detector substrate at the bottom of the x-ray detector substrate assuming the top is where the x-rays enter, and the associated anti-scatter collimator (20) is placed above the integrated circuit (30).
2. The detector module of claim 1, wherein the integrated circuits are Application Specific Integrated Circuits, ASICs.
3. The detector module of claim 2, wherein the ASIC is extending over the edge of the x-ray detector substrate so that part of the ASIC is outside of the silicon detector substrate to enable connection of power and data transfer to the ASIC without having to route this on the silicon detector substrate.
4. The detector module of claim 2 or 3, wherein signals are routed from the individual diodes to inputs of the ASIC.
5. The detector module of any of the claims 2 to 4, wherein power lines and data transfer lines are wire-bonded to power and data transfer pads at the ASIC outside the substrate, or a redistribution layer on the substrate is used to connect to power, data transfer pads and to input signal pads and redistribute the input signals from the x-ray detector substrate to the ASIC.
6. The detector module of any of the claims 2 to 5, wherein a heat conductor is attached to the ASIC as a means for cooling.

7. The detector module of any of the claims 1 to 6, wherein the anti-scatter collimators are anti-scatter foils.
8. The detector module of claim 7, wherein the anti-scatter foils are positioned between the x-ray detector substrates.
9. The detector module of claim 7 or 8, wherein the anti-scatter foils are made of a heavy material such as Tungsten.
10. The detector module of any of the claims 1 to 9, wherein the integrated circuits are Application Specific Integrated Circuits, ASICs, and the anti-scatter collimators are Tungsten foils and the ASICs are placed on the x-ray detector substrate under the Tungsten foils to minimize so-called dead area in the detector and the ASICs will be protected from direct radiation.
11. The detector module of any of the claims 1 to 10, wherein a tapered geometry in which, for each x-ray detector substrate, the x-ray detector substrate and the associated anti-scatter collimator are pointing back to the source is provided by means of a spacer placed at the silicon detector substrate or at the anti-scatter collimator.
12. The detector module of any of the claims 1 to 11, wherein a number of x-ray detector substrates are tiled with respect to each other to form a detector module.
13. The detector module of any of the claims 1 to 12, wherein each x-ray detector substrate and corresponding integrated circuit is formed as a sensor multi-chip module, MCM, assembly, and a multitude of sensor MCM assemblies are connected into the detector module.
14. The detector module of claim 13, wherein the detector module is subdivided into a number of detector tiles, where each detector tile includes a number of sensor MCM assemblies.

15. The detector module of claim 14, wherein each detector tile includes a circuit for demultiplexing commands from the corresponding detector module to the detector tile to reduce the number of connections between the detector tile and the detector module.
16. The detector module of claim 15, wherein the commands are control commands directed to the sensor MCM assemblies.
17. The detector module of any of the claims 14 to 16, wherein the detector module comprises a number of data storage circuits and data processing circuits, wherein each detector tile is managed by a data processing circuit.
18. The detector module of claim 17, wherein the detector module includes a control and communication circuit for distributing control commands for the sensor MCM assemblies and controlling the readout of stored scanning data from the data storage circuits.
19. The detector module of any of the claims 1 to 18, wherein the x-ray detector substrates are Silicon detector substrates.
20. A modular x-ray detector (100) having a number of detector modules (1) of any of the claims 1 to 19.

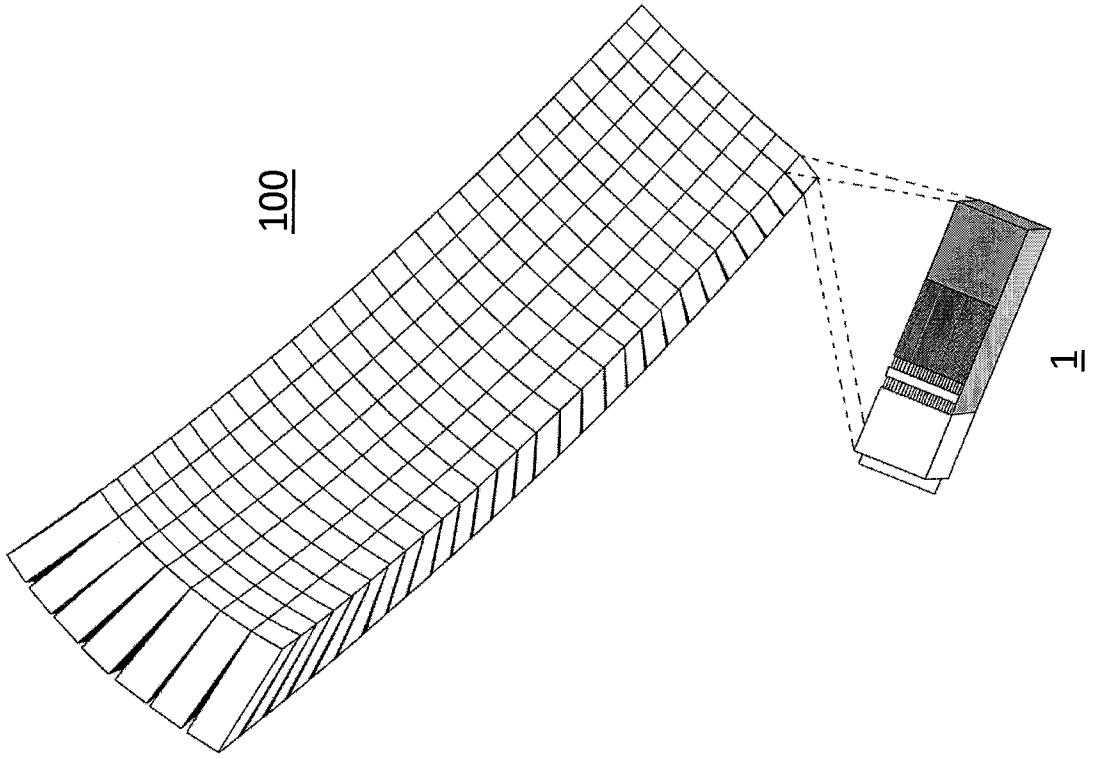


Fig 1

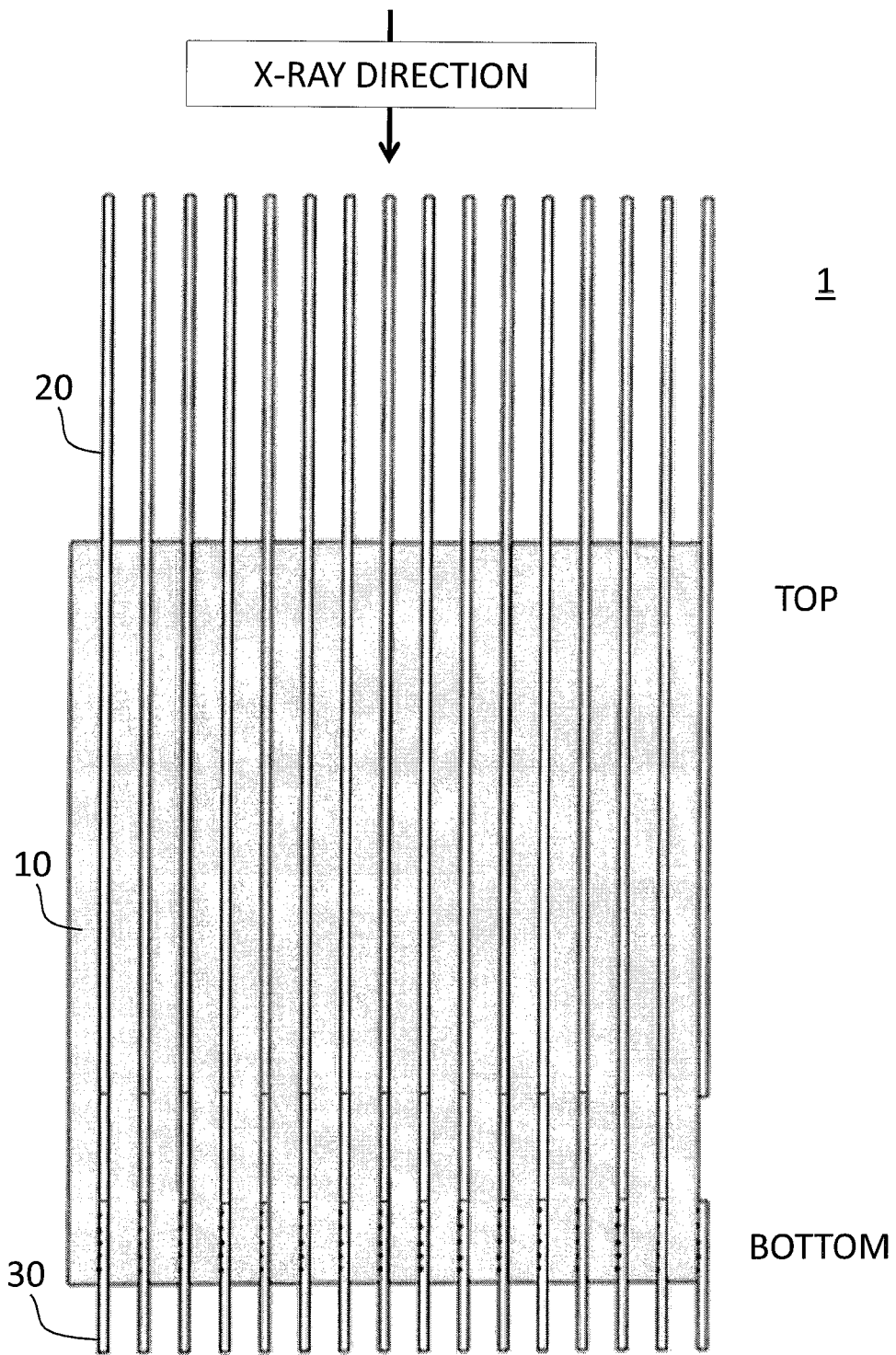


Fig 2

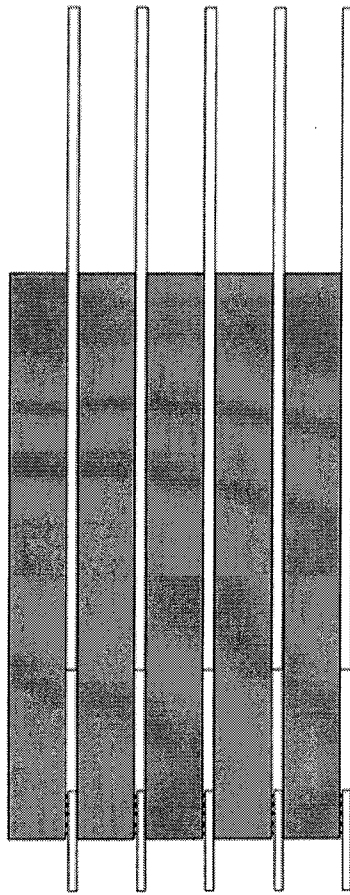


Fig 3

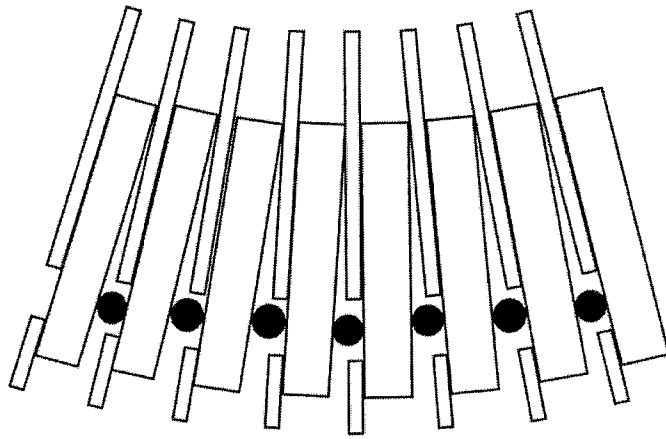
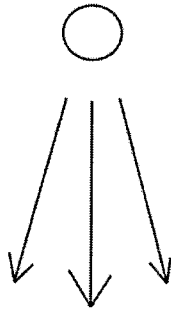


Fig 4

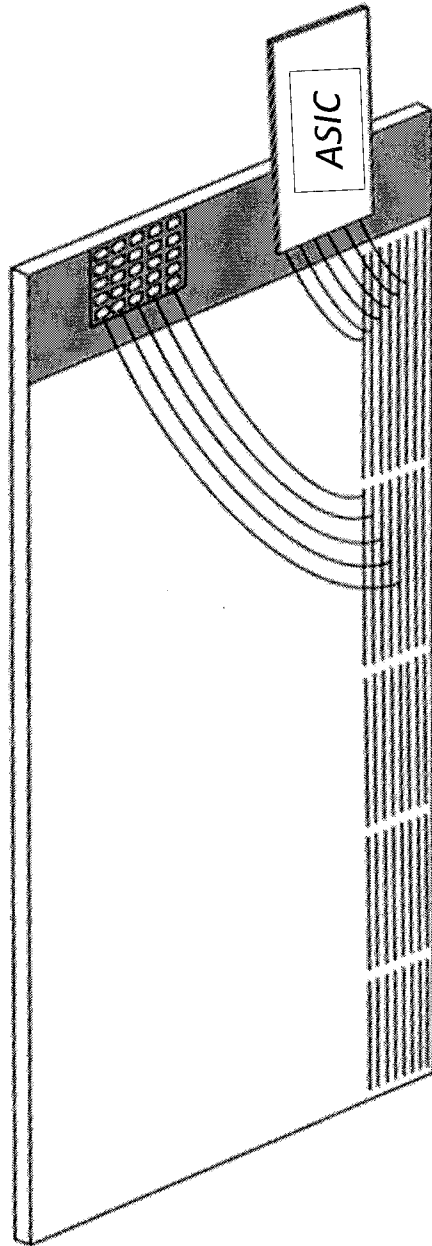


Fig 5

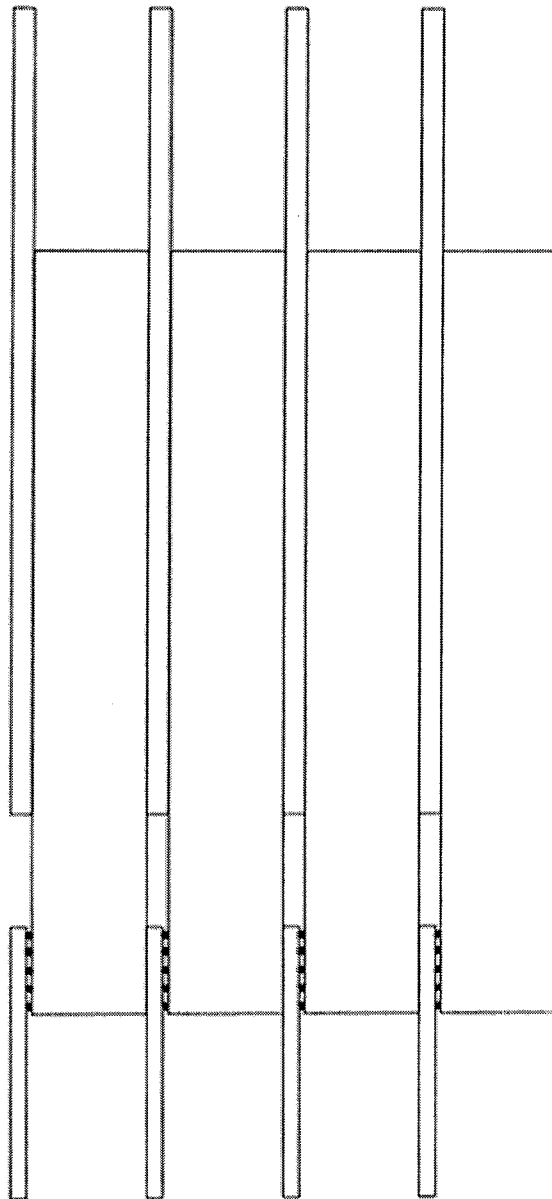
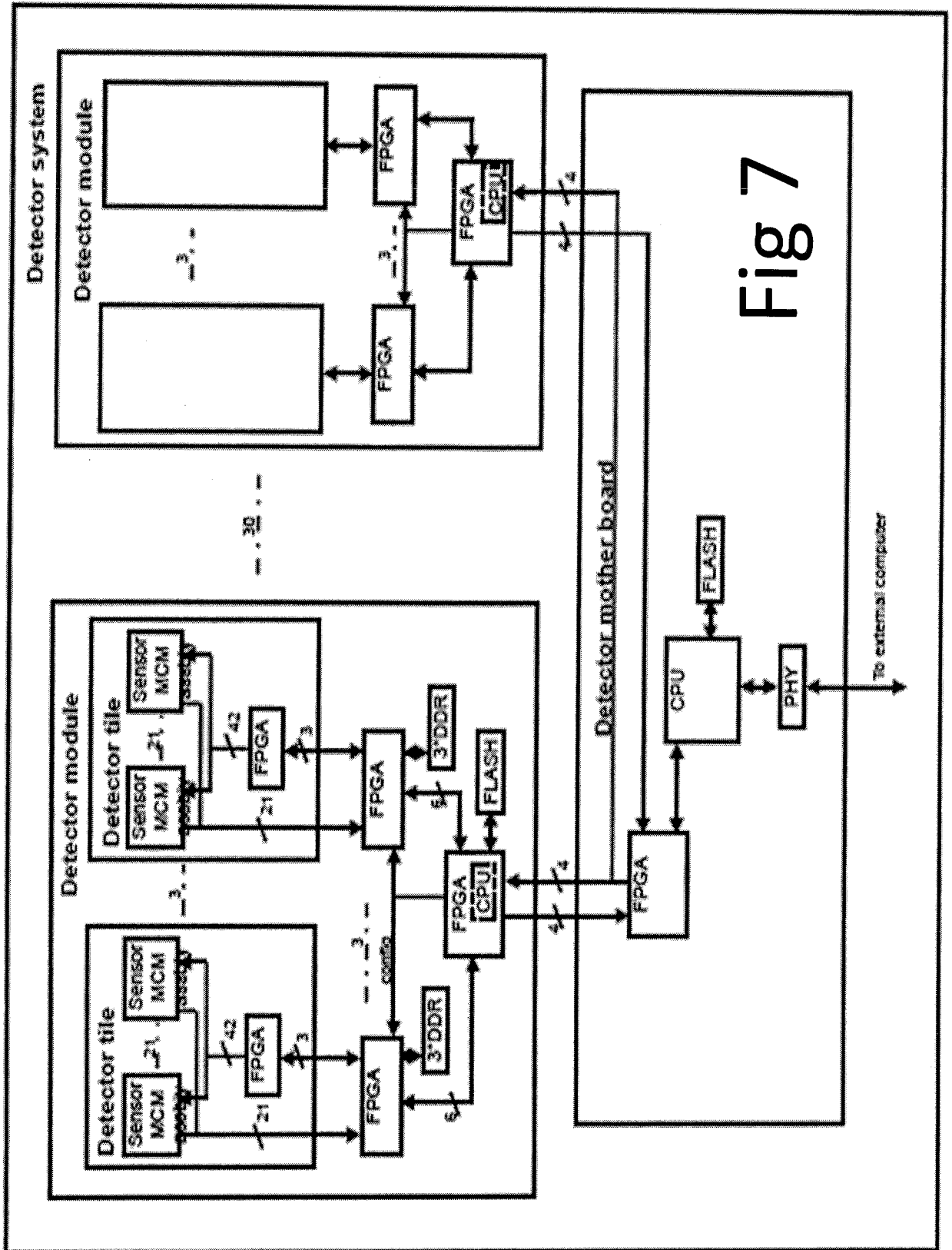


Fig 6



INTERNATIONAL SEARCH REPORT

International application No.
PCT/SE2016/050829

A. CLASSIFICATION OF SUBJECT MATTER		
IPC: see extra sheet		
According to International Patent Classification (IPC) or to both national classification and IPC		
B. FIELDS SEARCHED		
Minimum documentation searched (classification system followed by classification symbols)		
IPC: G01T, G21K		
Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched		
SE, DK, FI, NO classes as above		
Electronic data base consulted during the international search (name of data base and, where practicable, search terms used)		
EPO-Internal, PAJ, WPI data, COMPENDEX, EMBASE, INSPEC		
C. DOCUMENTS CONSIDERED TO BE RELEVANT		
Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
X	US 20080283760 A1 (TSUCHIYA KATSUTOSHI ET AL), 20 November 2008 (2008-11-20); paragraphs [0066]-[0067], [0089]-[0090], [0092]-[0093]; figures 6,22A,22B	1-2, 4-9, 12, 19-20
A	--	3, 10-11, 13-18
X	US 20110122998 A1 (KONINKL PHILIPS ELECTRONICS NV ET AL), 11 February 2010 (2010-02-11); paragraphs [0001]-[0002], [0010]-[0011]; figures	1-2, 4-9, 12
A	--	3, 10-11, 13-20
<input checked="" type="checkbox"/>	Further documents are listed in the continuation of Box C.	<input checked="" type="checkbox"/> See patent family annex.
* Special categories of cited documents:		
"A" document defining the general state of the art which is not considered to be of particular relevance		"T" later document published after the international filing date or priority date and not in conflict with the application but cited to understand the principle or theory underlying the invention
"E" earlier application or patent but published on or after the international filing date		"X" document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone
"L" document which may throw doubts on priority claim(s) or which is cited to establish the publication date of another citation or other special reason (as specified)		"Y" document of particular relevance; the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such documents, such combination being obvious to a person skilled in the art
"O" document referring to an oral disclosure, use, exhibition or other means		"&" document member of the same patent family
"P" document published prior to the international filing date but later than the priority date claimed		
Date of the actual completion of the international search	Date of mailing of the international search report	
12-12-2016	13-12-2016	
Name and mailing address of the ISA/SE Patent- och registreringsverket Box 5055 S-102 42 STOCKHOLM Facsimile No. + 46 8 666 02 86	Authorized officer Fredrik Engdahl Telephone No. + 46 8 782 28 00	

INTERNATIONAL SEARCH REPORT

International application No.
PCT/SE2016/050829

C (Continuation). DOCUMENTS CONSIDERED TO BE RELEVANT		
Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
A	WO 2005096946 A1 (PHILIPS INTELLECTUAL PROPERTY ET AL), 20 October 2005 (2005-10-20); abstract; figures --	1-20
A	US 20100204942 A1 (DANIELSSON MATS ET AL), 12 August 2010 (2010-08-12); abstract; paragraphs [0042]-[0048]; figures 1-5 --	1-20
A	US 20020181647 A1 (VENKATARAMANI VENKAT SUBRAMANI ET AL), 5 December 2002 (2002-12-05); paragraphs [0040]-[0043]; figure 4 --	1-20
A	US 5144141 A (ROUGEOT HENRI M ET AL), 1 September 1992 (1992-09-01); abstract; figure 1 --	1-20
A	US 20140321609 A1 (LEVENE SIMHA ET AL), 30 October 2014 (2014-10-30); paragraphs [0020]-[0022], [0025]-[0026]; figures --	1-20
A	US 20140348290 A1 (HARRISON DANIEL DAVID ET AL), 27 November 2014 (2014-11-27); abstract; paragraph [0027] --	1-20
A	US 20140355734 A1 (YING ZHENGRONG), 4 December 2014 (2014-12-04); abstract; paragraphs [0014]-[0015]; figure 4b --	1-20
A	US 20070242804 A1 (PHILIPS INTELLECTUAL PROPERTY ET AL), 9 June 2005 (2005-06-09); paragraph [0036]; figures 1a, 2 --	1-20
A	Nagarkar et al., A modular high-resolution photon-counting x-ray detector, 29 December 2010, SPIE Newsroom, DOI: 10.1117/2.1201011.003217; whole document --	1-20
A	Xu et al., IEEE TRANSACTIONS ON NUCLEAR SCIENCE, VOL. 58, NR. 3, PG 614-625, 2011-06-01, ISSN 0018-9499; whole document --	1-20

INTERNATIONAL SEARCH REPORT

International application No.
PCT/SE2016/050829

C (Continuation). DOCUMENTS CONSIDERED TO BE RELEVANT		
Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
A	Fitrio et al., Integrated Circuits, ISIC '09. Proceedings of the 2009 12th International Symposium, pg 179 - 182, 2009-12-14, ISBN 978-981-08-2468-6; whole document -- -----	1-20

INTERNATIONAL SEARCH REPORT

Information on patent family members

International application No.

PCT/SE2016/050829

US	20080283760 A1	20/11/2008	EP	1408347 A1	14/04/2004
			EP	1852716 A3	14/11/2007
			KR	100689177 B1	08/03/2007
			KR	100665144 B1	09/01/2007
			KR	20060107486 A	13/10/2006
			KR	20040031648 A	13/04/2004
			US	7119340 B2	10/10/2006
			US	7115877 B2	03/10/2006
			US	20060261281 A1	23/11/2006
			US	20040217293 A1	04/11/2004
			US	20040104350 A1	03/06/2004
			US	7745795 B2	29/06/2010
			US	7378662 B2	27/05/2008
			US	20110122998 A1	11/02/2010
EP	2321668 B1	25/03/2015			
JP	2011530081 A	15/12/2011			
JP	5616340 B2	29/10/2014			
RU	2011108494 A	20/09/2012			
RU	2506609 C2	10/02/2014			
US	8426826 B2	23/04/2013			
WO	2010015959 A3	04/11/2010			
WO	2005096946 A1	20/10/2005	AT	509578 T	15/06/2011
			CN	101027000 B	12/05/2010
			EP	1734865 B1	18/05/2011
			JP	2007532168 A	15/11/2007
			JP	4777975 B2	21/09/2011
			US	20080230706 A1	25/09/2008
			US	7525097 B2	28/04/2009
			US	20100204942 A1	12/08/2010
DE	112010000797 T5	12/07/2012			
GB	2480561 B	21/08/2013			
JP	2012517604 A	02/08/2012			
JP	5717652 B2	13/05/2015			
KR	20110126645 A	23/11/2011			
US	8183535 B2	22/05/2012			
WO	2010093314 A1	19/08/2010			
US	20020181647 A1	05/12/2002	US	20030021374 A1	30/01/2003
			US	7310405 B2	18/12/2007
			US	6519313 B2	11/02/2003
US	5144141 A	01/09/1992	NONE		

INTERNATIONAL SEARCH REPORT

Information on patent family members

International application No.

PCT/SE2016/050829

US	20140321609 A1	30/10/2014	CN	103959098 A	30/07/2014
			EP	2751595 A2	09/07/2014
			IN	3832CHN2014 A	03/07/2015
			JP	2015503096 A	29/01/2015
			RU	2014126371 A	27/01/2016
			WO	2013080105 A2	06/06/2013
US	20140348290 A1	27/11/2014	NONE		
US	20140355734 A1	04/12/2014	CN	104161535 A	26/11/2014
			US	9076563 B2	07/07/2015
US	20070242804 A1	09/06/2005	CN	1886674 B	08/12/2010
			EP	1692544 A1	23/08/2006
			JP	2007512075 A	17/05/2007
			US	7465931 B2	16/12/2008
			WO	2005052636 A8	12/10/2006

Continuation of: second sheet

International Patent Classification (IPC)

G01T 1/24 (2006.01)

G01T 1/29 (2006.01)

G21K 1/10 (2006.01)

G21K 1/02 (2006.01)